

RECEIVED
JUL 14 2003
TC 1700



PATENT APPLICATION

#7/B
4/15/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q68148

Kuniaki YAGI, et al.

Appln. No.: 10/050,570

Group Art Unit: 1765

Confirmation No.: 7078

Examiner: SONG, MATTHEW

Filed: January 18, 2002

For: SINGLE CRYSTAL SIC AND METHOD OF PRODUCING THE SAME AS WELL AS
SIC SEMICONDUCTOR DEVICE AND SIC COMPOSITE MATERIAL

AMENDMENT UNDER 37 C.F.R. § 1.111

MAIL STOP NON-FEE AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated April 23, 2003, please amend the above-identified application as follows:

IN THE SPECIFICATION:

The specification is changed as follows:

Page 9, full paragraph No. 5,

B1
As the substrate, use can be made of Si, SiC, titanium carbide, diamond, or the like. The temperature at which the single crystal SiC layer is formed falls within the range between about 1000 and 1100°C in case where a Si substrate is used as the substrate. By heating the substrate to the above-mentioned temperature under existence of the substance containing C or C and Si, the single crystal SiC layer with high-quality having a film thickness of about 10 nm can relatively easily be formed (for example, see C. J. Mogab et al. Journal of Applied Physics Vol. 45 (1974) P1075-).